

深圳市晶泰源电子有限公司

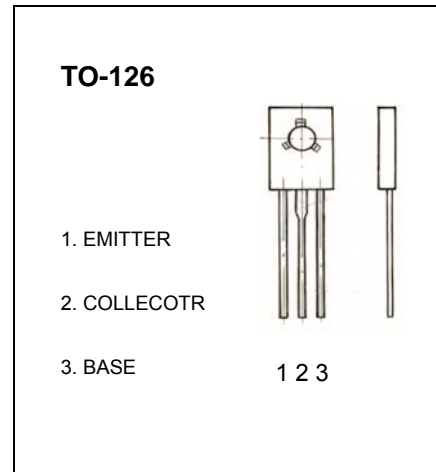
BD434,436 TRANSISTOR (PNP)

FEATURES

Amplifier and switching applications

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Units
V_{CBO}	Collector-Base Voltage	BD434	-22	V
		BD436	-32	
V_{CEO}	Collector-Emitter Voltage	BD434	-22	V
		BD436	-32	
V_{EBO}	Emitter-Base Voltage		-5	V
I_{C}	Collector Current –Continuous		-4	A
P_{C}	Collector Power Dissipation		1.25	W
T_{J}	Junction Temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{\text{amb}}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_{\text{C}}=-100\mu\text{A}, I_{\text{E}}=0$	BD434	-22		V
			BD436	-32		
Collector-emitter breakdown voltage	$V_{\text{CEO}}^{(\text{SUS})1}$	$I_{\text{C}}=-100\text{mA}, I_{\text{B}}=0$	BD434	-22		V
			BD436	-32		
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_{\text{E}}=-100\mu\text{A}, I_{\text{C}}=0$		-5		V
Collector cut-off current	I_{CBO}	$V_{\text{CB}}=-22\text{V}, I_{\text{E}}=0$	BD434		-100	μA
		$V_{\text{CB}}=-32\text{V}, I_{\text{E}}=0$	BD436			
Emitter cut-off current	I_{EBO}	$V_{\text{EB}}=-5\text{V}, I_{\text{C}}=0$			-1	mA
DC current gain	$h_{\text{FE}(1)}^{(1)}$	$V_{\text{CE}}=-5\text{V}, I_{\text{C}}=-10\text{mA}$		40		
	$h_{\text{FE}(2)}^{(1)}$	$V_{\text{CE}}=-1\text{V}, I_{\text{C}}=-500\text{mA}$		85	375	
	$h_{\text{FE}(3)}^{(1)}$	$V_{\text{CE}}=-1\text{V}, I_{\text{C}}=-2\text{A}$		50		
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}^{(1)}$	$I_{\text{C}}=-2\text{A}, I_{\text{B}}=-0.2\text{A}$			-0.5	V
Base-emitter voltage	$V_{\text{BE}}^{(1)}$	$V_{\text{CE}}=-1\text{V}, I_{\text{C}}=-2\text{A}$			-1.1	V
Transition frequency	f_{T}	$V_{\text{CE}}=-1\text{V}, I_{\text{C}}=-250\text{mA}$	3			MHz

⁽¹⁾Pulse test.